WE CLAIM AS OUR INVENTION:

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L	1)	Α	microsampling	device	comprising:

- a substrate defining a microsampler chamber; and
- a cuvette window formed of silicon nitride.
- 2) The device of Claim 1 wherein the substrate is silicon.
- 3) The device of Claim 2 wherein the silicon substrate has a thickness of approximately 500 micrometers.
- 4) The device of Claim 1 wherein the silicon nitride window has a thickness of approximately 0.01 to 5 micrometers.
- 5) The device of Claim 1 wherein the chamber has a volume of less than 1 micrometer.

	1	6) A method of constructing a cuvette window in the microsampler								
11 D of Davis ching (a,ph 1) "and Davis H D trade of the control of the contr	2	chamber of a microsampling device, the method comprising								
	3	providing a silicon wafer having a top surface and a								
	4	bottom surface;								
	5	etching a patterned depression in the top surface of the								
	6	silicon wafer thereby defining the microsampler chamber;								
	7	depositing a silicon nitride film on the top surface of								
	8	the silicon wafer; and								
	9	etching a patterned depression in the bottom surface of								
	10	the silicon wafer and exposing the silicon nitride film forming								
	11	the window.								
	1	7) The method of Claim 6 wherein the silicon wafer has a								
	2	thickness of approximately 500 micrometers.								
	1	8) The method of Claim 6 wherein the silicon nitride film has a								
H G B that and the	2	thickness of approximately 0.01 to 5 micrometers.								

- 9) A silicon device comprising:
- a silicon substrate defining a cuvette; and
- a cuvette window formed of silicon nitride.
- 10) The device of Claim 9 wherein the silicon nitride window has
- a thickness of approximately 0.01 to 5 micrometers.

A. Dong daya hand " "and Day 37 B Maret their fitt mare use " their than than	1	11)A method of constructing a window in the cuvette of a silicon
	2	device, the method comprising
	3	providing a silicon substrate having a top surface and a
	4	bottom surface;
	5	etching a patterned depression in the top surface of the
	6	silicon wafer thereby defining the cuvette;
	7	depositing a silicon nitride film on the top surface of
	8	the silicon wafer; and
	9	etching a patterned depression in the bottom surface of
	10	the silicon wafer and exposing the silicon nitride film forming
	11	the window.
	1	12) The method of Claim 12 wherein the substrate is a silicon
, P. Miller	2	wafer.
B H B Clark south You to the		13) The method of Claim 12 wherein the silicon nitride film has a
		thickness of approximately 0.01 to 5 micrometers.